

isc Silicon PNP Power Transistors

2SB696

DESCRIPTION

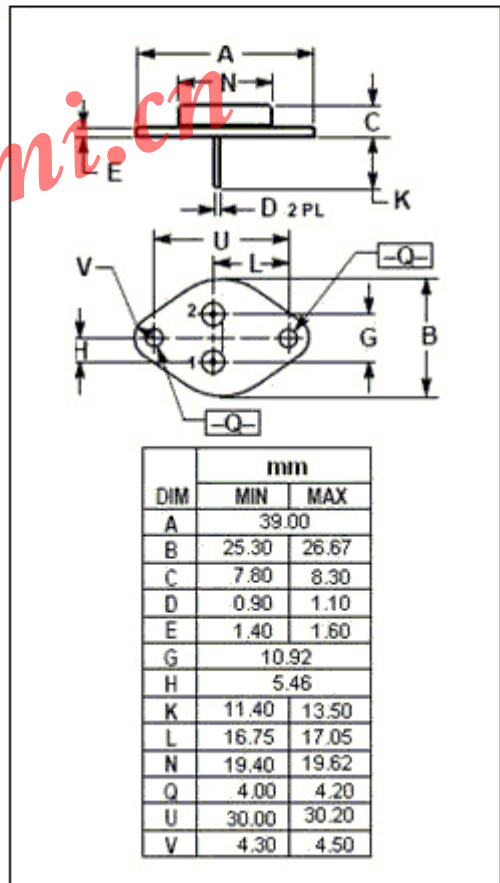
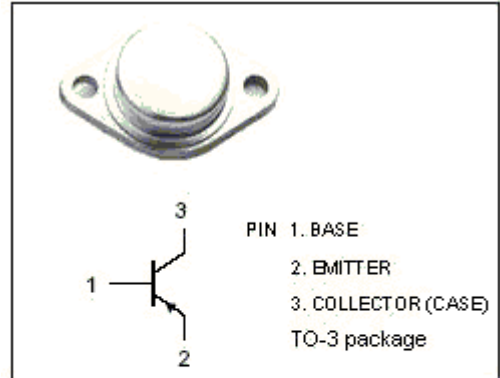
- Collector-Emitter Breakdown Voltage-
: $V_{(BR)CEO} = -120V(\text{Min})$
- High Current Capability
- Wide Area of Safe Operation
- Complement to Type 2SD732

APPLICATIONS

- Designed for AF power amplifier applications.
- Recommended for output stage of 60W power amplifier.

ABSOLUTE MAXIMUM RATINGS($T_a=25^\circ\text{C}$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	-150	V
V_{CEO}	Collector-Emitter Voltage	-120	V
V_{EBO}	Emitter-Base Voltage	-6	V
I_C	Collector Current-Continuous	-8	A
I_{CM}	Emitter Current-Peak	-12	A
P_C	Collector Power Dissipation @ $T_C=25^\circ\text{C}$	80	W
T_J	Junction Temperature	150	$^\circ\text{C}$
T_{stg}	Storage Temperature	-40~150	$^\circ\text{C}$



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ELECTRICAL CHARACTERISTICS

T_j=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CEO}	Collector-Emitter Breakdown Voltage	I _C = -5mA; R _{BE} = ∞	-120			V
V _{(BR)CEO}	Collector-Emitter Breakdown Voltage	I _C = -50mA; R _{BE} = ∞	-120			V
V _{(BR)CBO}	Collector-Base Breakdown Voltage	I _C = -5mA; I _E = 0	-150			V
V _{(BR)EBO}	Emitter-Base Breakdown Voltage	I _E = -5mA; I _C = 0	-6			V
V _{CE(sat)}	Collector-Emitter Saturation Voltage	I _C = -5A; I _B = -0.5A		-0.6		V
V _{BE(on)}	Base-Emitter On Voltage	I _C = -1A; V _{CE} = -5V			-1.5	V
I _{CBO}	Collector Cutoff Current	V _{CB} = -80V; I _E = 0			-0.1	mA
I _{EBO}	Emitter Cutoff Current	V _{EB} = -4V; I _C = 0			-0.1	mA
h _{FE}	DC Current Gain	I _C = -1A; V _{CE} = -5V	40		320	
f _T	Current-Gain—Bandwidth Product	I _C = -1A; V _{CE} = -5V		15		MHz

◆ h_{FE} Classifications

C	D	E	F
40-80	60-120	100-200	160-320